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TECHNICAL SPECIFICATION

Nanomanufacturing - Reliability assessment - Part 3-4: Linearity of output characteristics for metal contacted 2D semiconductor devices

Document Preview

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CONTENTS

Scope Normative references Terms and definitions	7 7
Normative references Terms and definitions	7
Terms and definitions	
0 4 0 0 0 0 0 1 1 1 1 1 1 1 1 1 1 1 1 1	7
3.1 General terms regarding the sample	7
3.2 General terms regarding the sample test	8
Recommended sample preparation	9
Device structure of the sample under test	9
I.2 Sample preparation method	9
· · ·	
Measurement procedure	11
5.1 Measurement equipment	11
Calibration of measurement equipment	11
Measurement procedure	11
ex A (informative) Worked example – Linearity of <i>I-V</i> curves for bottom-contacted WSe ₂ FETs	17
ex B (informative) Worked example – Linearity of <i>I-V</i> curves for edge-contacted	
_	
<u>1LC 15 020 / 0-3-T.2023</u>	
	2010 4 3
· · · · · · · · · · · · · · · · · · ·	23
· · · · · · · · · · · · · · · · · · ·	
9 4 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 -	
ure 1 – Metal–semiconductor (SC) junctions and their respective band diagrams	6
ure 2 – Schematic of a FET	8
re 3 – Schematic output curves obtained from ohmic and non-ohmic contact	12
	13
	14
ure A.1 – Device fabrication processing steps to induce ohmic-like transport by	10
	4.2.1 Sample preparation 4.2.2 Fabrication of FETs 4.2.3 Consideration on sample design Measurement procedure 5.1 Measurement equipment 5.2 Calibration of measurement equipment 5.3 Measurement procedure Data analysis / interpretation of results ex A (informative) Worked example – Linearity of I-V curves for bottom-contacted WSe2 FETs A.1 Background A.2 Results to be reported. ex B (informative) Worked example – Linearity of I-V curves for edge-contacted MoS2 FETs 3.1 Background 3.2 Results to be reported. 3.2 Results to be reported. 3.3 Background 3.4 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Background 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Background 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Background 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Results to be reported. 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Results to be reported. 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to be reported. 3.6 Results to be reported. 3.7 Results to be reported. 3.8 Results to be reported. 3.9 Results to be reported. 3.1 Results to be reported. 3.2 Results to be reported. 3.3 Results to be reported. 3.4 Results to be reported. 3.5 Results to

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Figure A.2 – (a), (b) Output curves and (c), (d) corresponding linearities collected from pristine and plasma-treated WSe ₂ FET at various V_{G}	18
Figure A.3 – Time dependent output curves and corresponding linearities collected from pristine and plasma-treated WSe ₂ FETs for various gate voltages applied	19
Figure B.1 – Cross-sectional view of edge-contact interface formed between MoS ₂ and metal that was used to induce ohmic-like contact	20
Figure B.2 – (a, b) Output curves and (c, d) corresponding linearities collected from Pd and Sb edge-contacted MoS_2 FETs with various gate voltages applied	21
Figure B.3 – (a-c) Time dependent output curves and (d) corresponding linearities collected from pristine and aged Sb edge-contacted MoS $_2$ FETs for various V_g	22
Figure C.1 – (a, d) Output curve, (b, e) the first derivative curve (dI_D/dV_D) and (c, f) linearity for devices with channel thicknesses of 2,1 nm and 7 nm, respectively	23
Table 1 – Allowed channel lengths to apply this document when contact resistance is limited up to 20 % and 50 %	11

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<u>IEC TS 62876-3-4:2025</u>

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